

HIGH VOLTAGE FAST SWITCHING NPN POWER TRANSISTOR

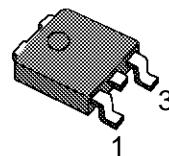
- SGS-THOMSON PREFERRED SALESTYPE
- HIGH VOLTAGE CAPABILITY
- SURFACE-MOUNTING TO-252 (DPAK)
POWER PACKAGE IN TAPE & REEL
(SUFFIX "T4")
- ELECTRICAL SIMILAR TO TIP47

APPLICATIONS

- SWITCH MODE POWER SUPPLIES
- AUDIO AMPLIFIERS
- GENERAL PURPOSE SWITCHING AND AMPLIFIER

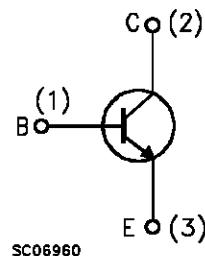
DESCRIPTION

The MJD47 is manufactured using Medium Voltage Epitaxial Planar technology, resulting in a rugged high performance cost-effective transistor.



**DPAK
TO-252
(Suffix "T4")**

INTERNAL SCHEMATIC DIAGRAM



SC06960

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{CBO}	Collector-Base Voltage ($I_E = 0$)	350	V
V _{CEO}	Collector-Emitter Voltage ($I_B = 0$)	250	V
V _{EBO}	Emitter-Base Voltage ($I_C = 0$)	5	V
I _C	Collector Current	1	A
I _{CM}	Collector Peak Current ($t_p < 5 \text{ ms}$)	2	A
I _B	Base Current	0.6	A
I _{BM}	Base Peak Current ($t_p < 5 \text{ ms}$)	1.2	A
P _{tot}	Total Dissipation at $T_c = 25^\circ\text{C}$	15	W
T _{stg}	Storage Temperature	-65 to 150	°C
T _j	Max. Operating Junction Temperature	150	°C

THERMAL DATA

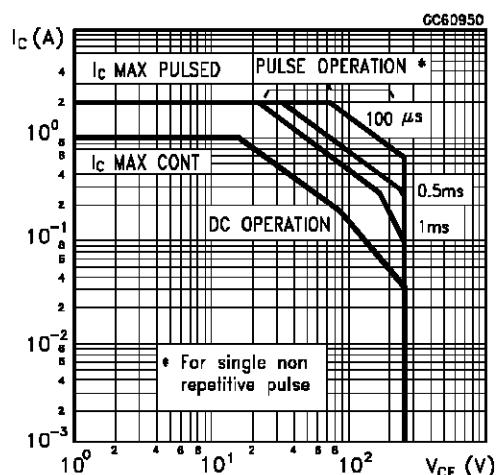
$R_{\text{thj-case}}$	Thermal Resistance Junction-case	Max	8.33	$^{\circ}\text{C}/\text{W}$
$R_{\text{thj-amb}}$	Thermal Resistance Junction-ambient	Max	100	$^{\circ}\text{C}/\text{W}$

ELECTRICAL CHARACTERISTICS ($T_{\text{case}} = 25^{\circ}\text{C}$ unless otherwise specified)

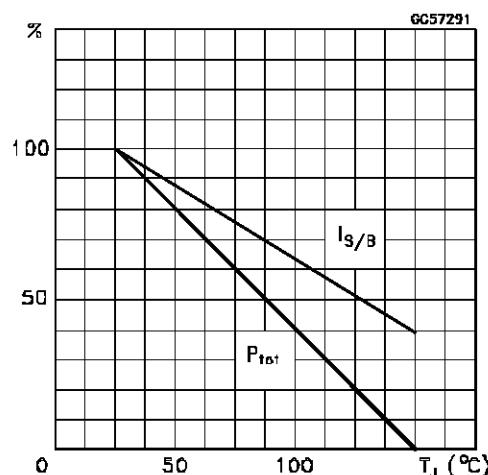
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{CES}	Collector Cut-off Current ($V_{\text{BE}} = 0$)	$V_{\text{CE}} = 350 \text{ V}$			0.1	mA
I_{CEO}	Collector Cut-off Current ($I_B = 0$)	$V_{\text{CE}} = 150 \text{ V}$			0.2	mA
I_{EBO}	Emitter Cut-off Current ($I_C = 0$)	$V_{\text{EB}} = 5 \text{ V}$			1	mA
$V_{\text{CEO(sus)}}$	Collector-Emitter Sustaining Voltage	$I_C = 30 \text{ mA}$	250			V
$V_{\text{CE(sat)*}}$	Collector-Emitter Saturation Voltage	$I_C = 1 \text{ A} \quad I_B = 0.2 \text{ A}$			1	V
$V_{\text{BE(on)*}}$	Base-Emitter On Voltage	$I_C = 1 \text{ A} \quad V_{\text{CE}} = 10 \text{ V}$			1.5	V
$h_{\text{FE}*}$	DC Current Gain	$I_C = 0.3 \text{ A} \quad V_{\text{CE}} = 10 \text{ V}$ $I_C = 1 \text{ A} \quad V_{\text{CE}} = 10 \text{ V}$	30 10		150	
f_T	Transition Frequency	$I_C = 200 \text{ mA} \quad V_{\text{CE}} = 10 \text{ V} \quad f=2\text{MHz}$	10			MHz
h_{fe}	Small Signal Current Gain	$I_C = 0.2 \text{ A} \quad V_{\text{CE}} = 10 \text{ V} \quad f=1\text{kHz}$	25			

* Pulsed: Pulse duration = 300 μs , duty cycle 1.5 %

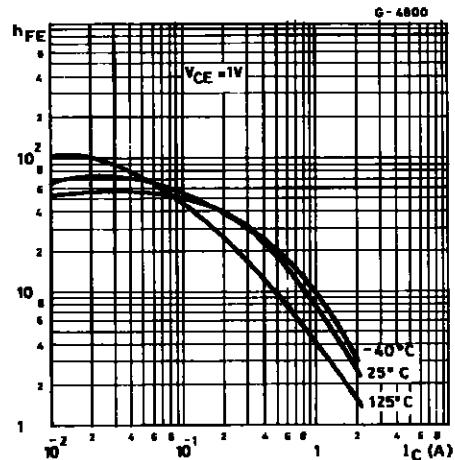
Safe Operating Areas



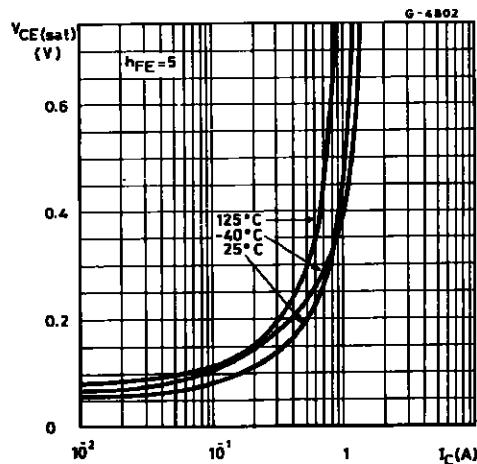
Derating Curves



DC Current Gain

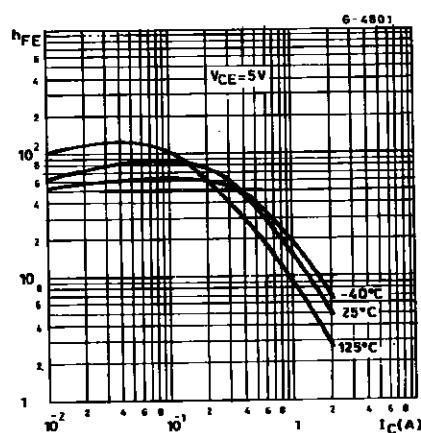


Collector-Emitter Saturation Voltage

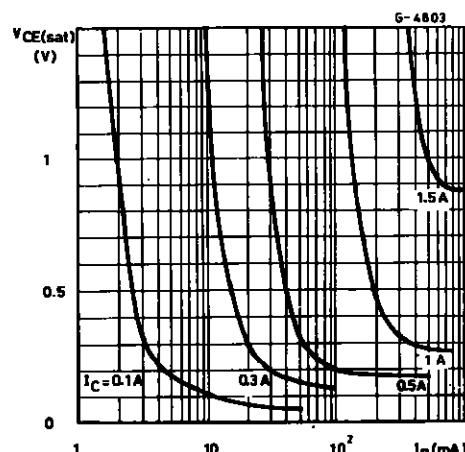


Base-Emitter Saturation Voltage

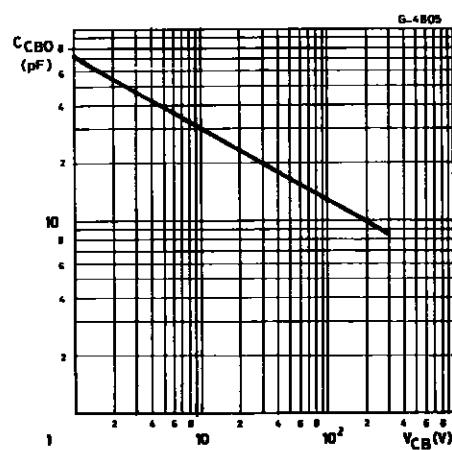
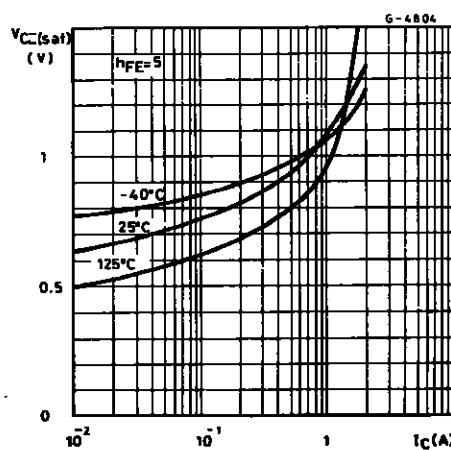
DC Current Gain



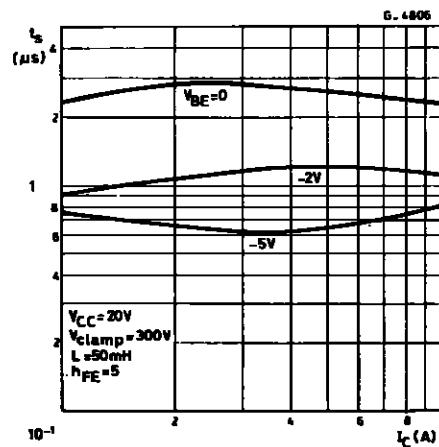
Collector-Emitter Saturation Voltage



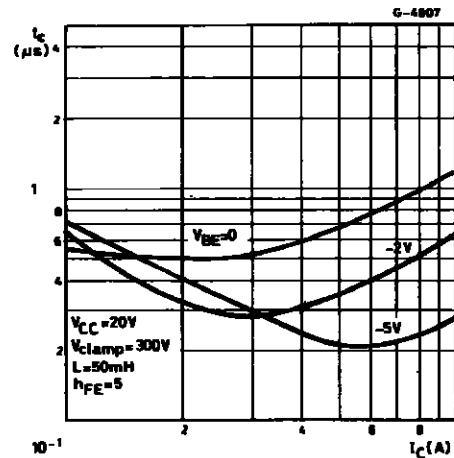
Collector-Base Capacitance



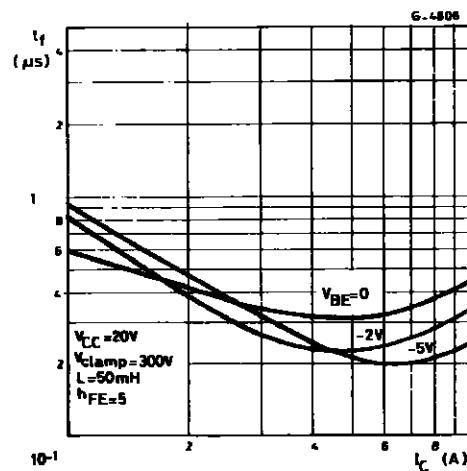
Switching Time Inductive Load



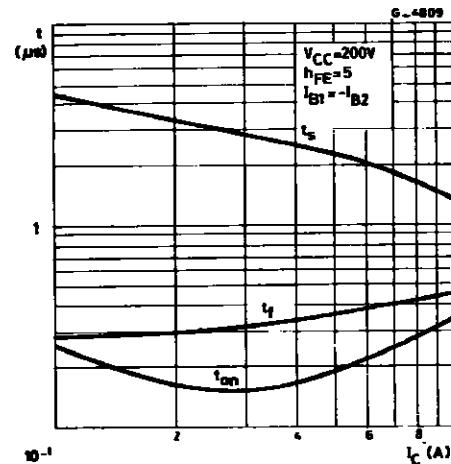
Switching Time Inductive Load



Switching Time Inductive Load

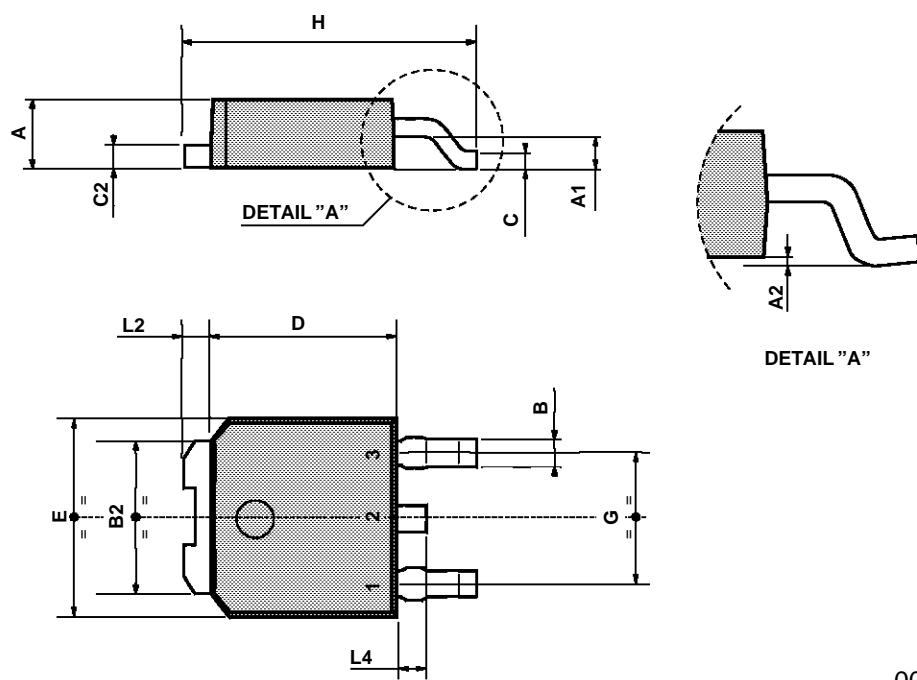


Switching Time Inductive Load



TO-252 (DPAK) MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	2.2		2.4	0.086		0.094
A1	0.9		1.1	0.035		0.043
A2	0.03		0.23	0.001		0.009
B	0.64		0.9	0.025		0.035
B2	5.2		5.4	0.204		0.212
C	0.45		0.6	0.017		0.023
C2	0.48		0.6	0.019		0.023
D	6		6.2	0.236		0.244
E	6.4		6.6	0.252		0.260
G	4.4		4.6	0.173		0.181
H	9.35		10.1	0.368		0.397
L2		0.8			0.031	
L4	0.6		1	0.023		0.039



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